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A first embodiment of the present invention will now be described in detail using to Fig. 6 to Fig. 8. First of all, an insulating film 21 (for example SiO_2 , BPSG) is deposited on a semiconductor substrate 20. Next, a Ti film 22, for example, is deposited to a thickness of 50 nm, as a barrier layer. An Al film 24 is then deposited to a thickness of 400 – 800 nm by a sputter method using an Al-1.0% Si-0.5% Cu target. The temperature when this Al film is deposited is a least 400°C.

(2.) At page 12, please replace the “ABSTRACT OF THE DISCLOSURE” with the following:

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ABSTRACT OF THE DISCLOSURE

An Al_3Ti film having a large amount of dissolved Si is deposited on a semiconductor substrate to form a laminate with an Al wiring film, and heat treatment is performed at a temperature of at least 400°C, to thereby absorb excessive Si into the Al_3Ti film and so prevent the occurrence of Si nodules. By depositing Al film at a temperature of at least 400°C at the time of depositing the Al wiring film on the Al_3Ti film, excessive Si is caused to be absorbed in the Al_3Ti film. Further, at the time of depositing a Ti film on the semiconductor substrate and depositing the Al wiring film, the Al film is deposited at a temperature of a least 400°C, there is reaction between the Ti film within the laminate, causing an Al_3Ti film to be produced, and excessive Si is absorbed in the Al_3Ti film produced.

In the Claims

(1). Please amend the claims as follows: